

**SOT-363 Plastic-Encapsulate Diodes****BAT54TW/ADW/CDW/SDW/BRW**

SCHOTTKY DIODE

FEATURES

Power dissipation

 P_D : 200 mW ($T_{amb}=25^{\circ}C$)

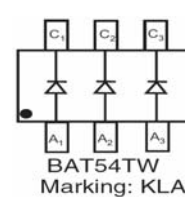
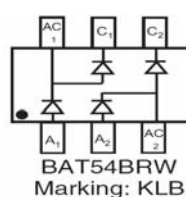
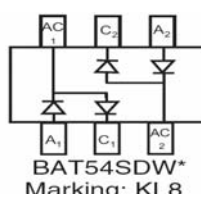
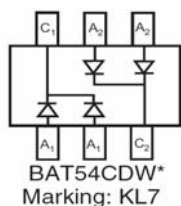
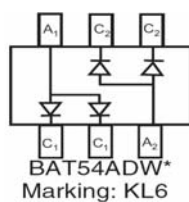
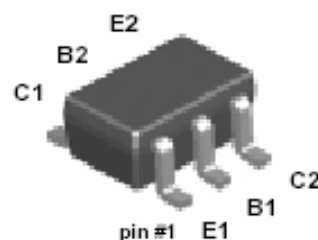
Forward Current

 I_F : 200 mA

Reverse Voltage

 V_R : 30 V

Operating and storage junction temperature range

 T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$ **SOT-363****ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	30		V
Reverse voltage leakage current	I_R	$V_R=25V$		2	μA
Forward voltage	V_F	$I_F=0.1mA$ $I_F=1mA$ $I_F=10mA$ $I_F=30mA$ $I_F=100mA$		240 320 400 500 1000	mV
Diode capacitance	C_D	$V_R=1V, f=1MHz$		10	pF
Reverse recovery time	t_{rr}	$I_F=10mA$ through $I_R=10mA$ to $I_R=1.0mA$ $R_C=100\Omega$		5	nS